



DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

Device	BV _{DSS}	Rds(on) max	I _{D MAX} T _A = +25°C
		$61m\Omega @ V_{GS} = -4.5V$	-3.8A
P-Channel	-12V	81mΩ @ V _{GS} = -2.5V	-3.3A
		115mΩ @ V _{GS} = -1.8V	-2.8A

Features

- Low On-Resistance
- Low Input Capacitance
- · Low Profile, 0.6mm Max Height
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Description

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

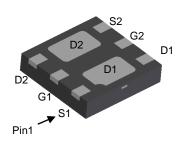
Applications

- Load Switch
- Power Management Functions
- Portable Power Adaptors

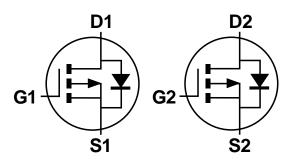
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 4
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

U-DFN2020-6 (Type B)



Bottom View



Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP1046UFDB -7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMP1046UFDB -13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1



P6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	С		Н	ı	J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



P6 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Date Code Key												
Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	5		0	1	2	3	4	5	6	7	8	9
Week		1.	-26			27	-52			5	3	
Code		Α	۱-Z			a	-Z			7	7	
Internal Code	Sur	1	Mon		Tue	W	ed	Thu		Fri		Sat
Code	Т		U		V	V	٧	Х		Υ		Z



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		VDSS	-12	V	
Gate-Source Voltage		V_{GSS}	±8	V	
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	lσ	-3.8 -3.0	А
Continuous Diain Current (Note 5) VGS = -4.5V	t < 5s	T _A = +25°C T _A = +70°C	lο	-5.0 -4.0	А
Maximum Continuous Body Diode Forward Curre	nt (Note 5)		Is	-1	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	l%)	I _{DM}	-15	Α	
Avalanche Current (L = 0.1mH)		I _{AS}	-12	Α	
Avalanche Energy (L = 0.1mH)			Eas	8	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 5)	Steady State	D-	1.4	W	
Total Fower Dissipation (Note 3)	t < 5s	PD	2.2	VV	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Steady State			
Thermal Resistance, Junction to Ambient (Note 5)	t < 5s	RθJA	55	°C/W	
Thermal Resistance, Junction to Case (Note 5)	R ₀ JC	20			
Operating and Storage Temperature Range		TJ, TSTG	-55 to 150	°C	

Note: 5. Device mounted on 1" × 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

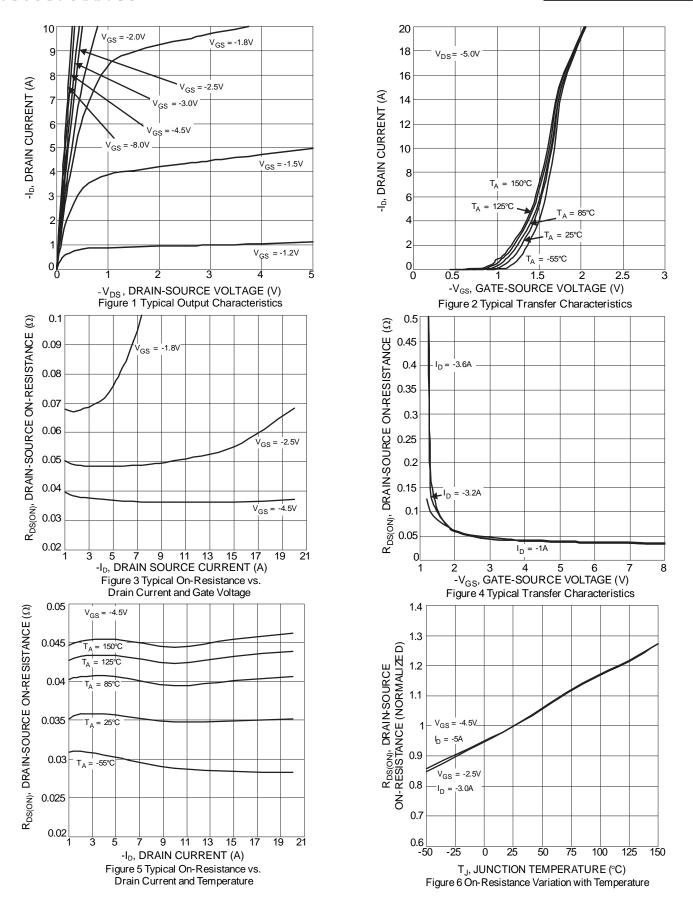
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	-12	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	-1.0	μA	V _{DS} = -12V, V _{GS} = 0V
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	Vgs(TH)	-0.4		-1	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
			37	61		$V_{GS} = -4.5V$, $I_{D} = -3.6A$
Static Drain-Source On-Resistance	R _{DS(ON)}		47	81	$m\Omega$	$V_{GS} = -2.5V$, $I_D = -3.2A$
			63	115		$V_{GS} = -1.8V, I_{D} = -1.0A$
Diode Forward Voltage	V_{SD}	_	-0.65	-1.2	V	$V_{GS} = 0V, I_{S} = -4.5A$
DYNAMIC CHARACTERISTICS (Note 7)	•			•		
Input Capacitance	Ciss		915		рF)/ O)/)/
Output Capacitance	Coss	_	225	_	pF	V _{DS} = -6V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss		183	_	pF	1 = 1.0lvii iz
Gate Resistance	Rg		56.9	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (VGS = -4.5V)	0		10.7	_	nC	
Total Gate Charge (V _{GS} = -8V)	Qg	_	17.9	_	nC	V _{DS} = -6V. I _D = -4.3A
Gate-Source Charge	Qgs		1.7	_	nC	$V_{DS} = -6V, I_{D} = -4.3A$
Gate-Drain Charge	Qgd	_	3.0	_	nC	
Turn-On Delay Time	td(ON)	_	5.7	_	ns	
Turn-On Rise Time	t _R		11.5	_	ns	$V_{DD} = -6V, V_{GS} = -4.5V,$
Turn-Off Delay Time	tD(OFF)		27.8	_	ns	$R_L = 1.6\Omega$, $R_G = 1\Omega$
Turn-Off Fall Time	t _F		26.4	_	ns]

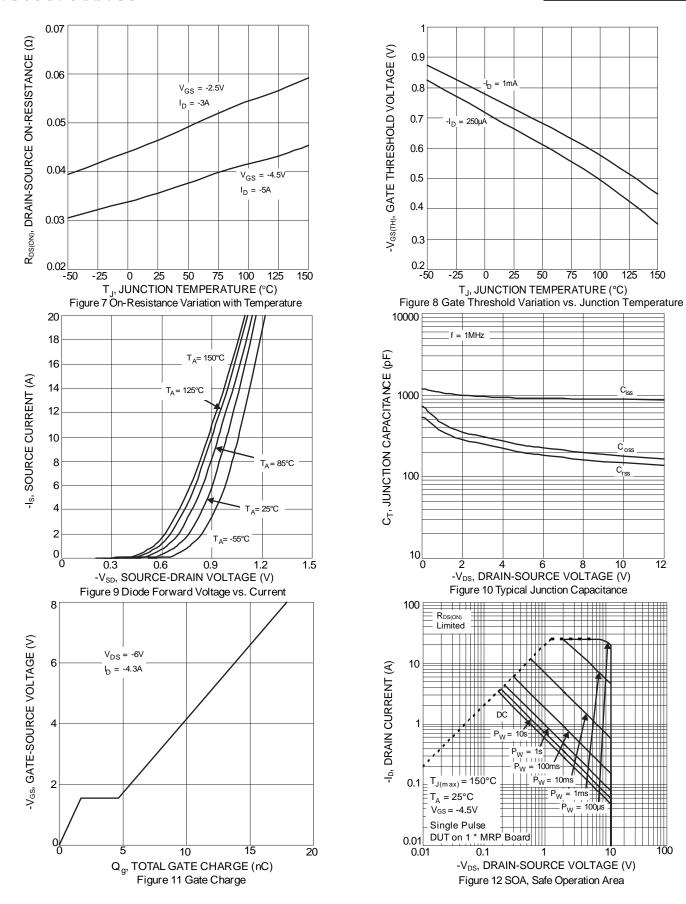
Notes: 6. Short duration pulse test used to minimize self-heating effect.

7. Guaranteed by design. Not subject to product testing.

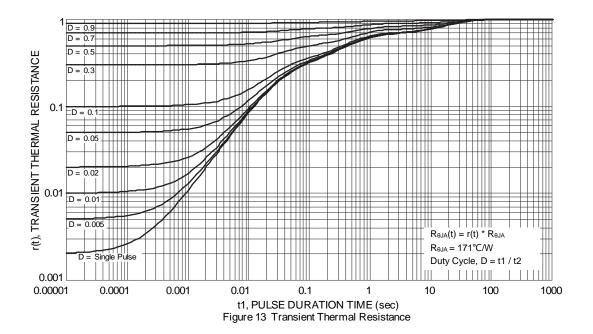










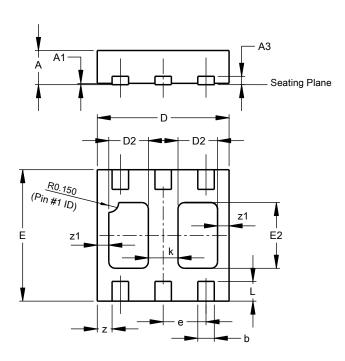




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

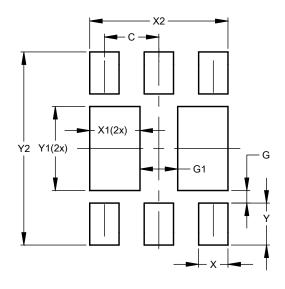


	U-DFN2020-6 Type B						
Dim	Min						
Α	0.545	0.605	0.575				
A 1	0.00	0.05	0.02				
А3	-	-	0.13				
b	0.20	0.30	0.25				
D	1.95	2.075	2.00				
D2	0.50	0.70	0.60				
е	-	-	0.65				
Е	1.95	2.075	2.00				
E2	0.90	1.10	1.00				
k	-	-	0.45				
L	0.25	0.35	0.30				
Z	-	-	0.225				
z1	-	-	0.175				
All	Dimens	ions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value
	(in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300



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